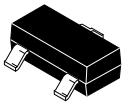
i,i o Hb -C i Dio!

Schottky Barrier Diodes

BD701, BD701L, BD701L

TO−92 2−Lead
CASE 182
STYLE 1



SOT−23 (TO−236)
CASE 318
STYLE 8

These devices are designed primarily for high−efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low−cost, high−volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

Features

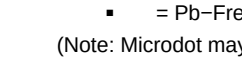
- Extremely Low Minority Carrier Lifetime − 15 ps (Typ)
- Very Low Capacitance − 1.0 pF @ V_R = 20 V
- High Reverse Voltage − to 70 V
- Low Reverse Leakage − 200 nA (Max)
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS

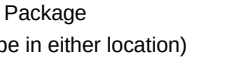
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Power Dissipation @ T_A = 25°C MBD701 MMBD701L, SMMBD701L Derate above 25°C MBD701 MMBD701L, SMMBD701L	P_F	 280 200 2.8 2.0	mW mW/°C
Operating Junction Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

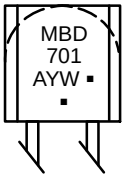
TO−92



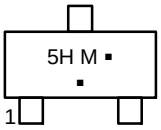
SOT−23



MARKING DIAGRAMS



TO−92



SOT−23

A = Assembly Location
Y = Year
W = Work Week
5H = Device Code (SOT−23)
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

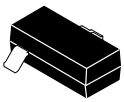
Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)R}$	70	–	–	V
Total Capacitance (V_R = 20 V, f = 1.0 MHz) Figure 1	C_T	–	0.5	1.0	pF
Reverse Leakage (V_R = 35 V) Figure 3	I_R	–	9.0	200	nAdc
Forward Voltage (I_F = 1.0 mAdc) Figure 4	V_F	–	0.42	0.5	Vdc
Forward Voltage (I_F = 10 mAdc) Figure 4	V_F	–	0.7	1.0	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package

-



SCALE 4:1

SOT 23 (TO 236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

SOT 23 (TO 236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE
3.